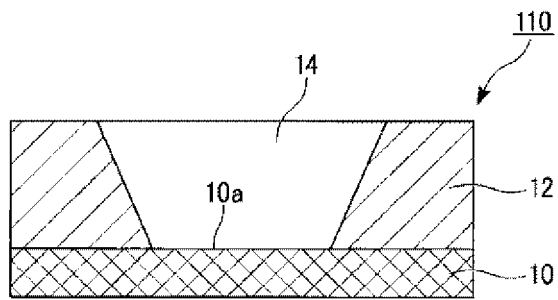
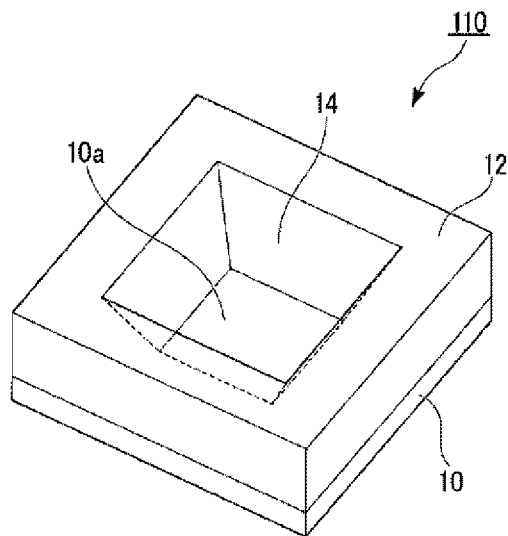


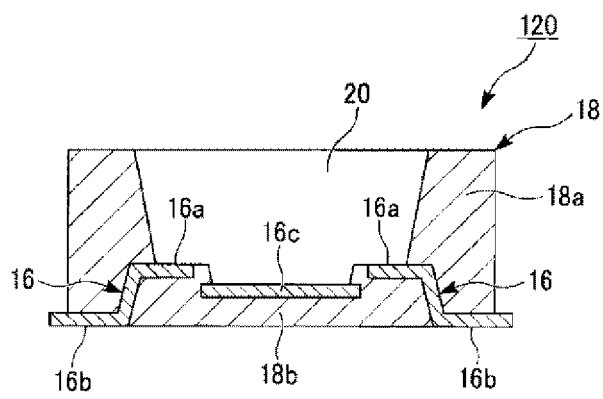
[図1]



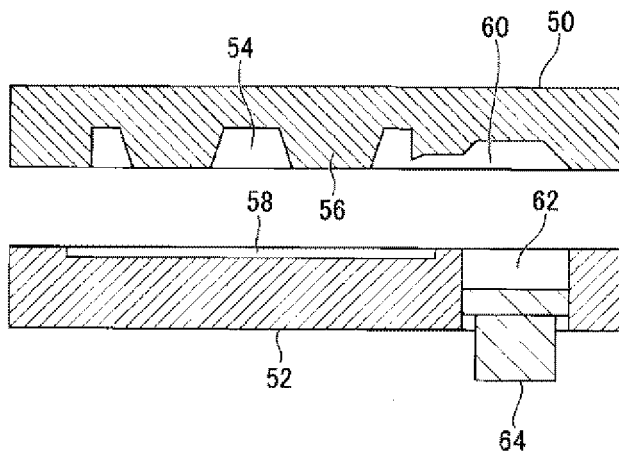
[図2]



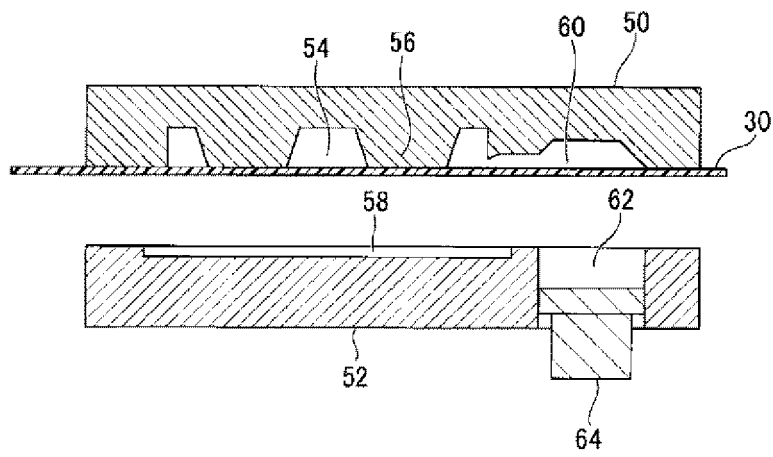
[図3]



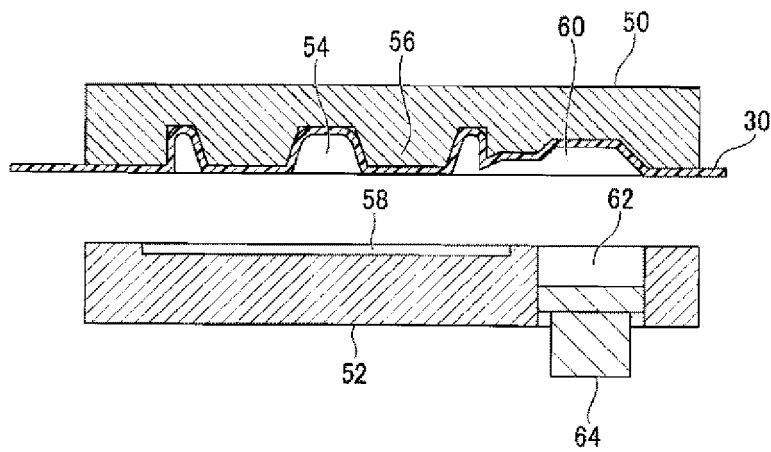
[図4]



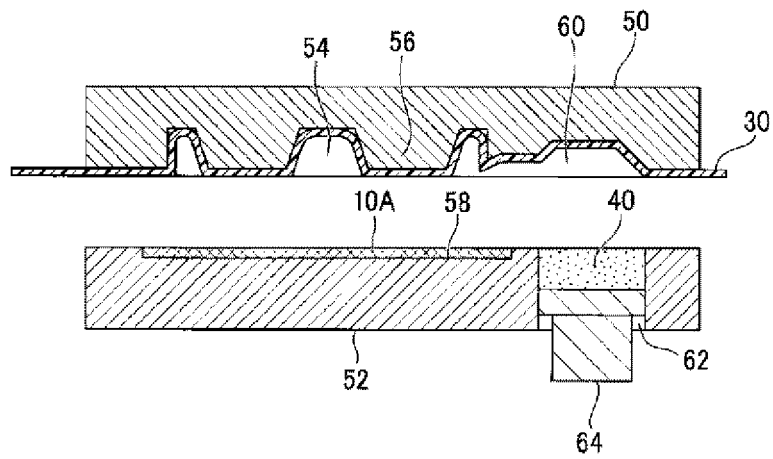
[図5]



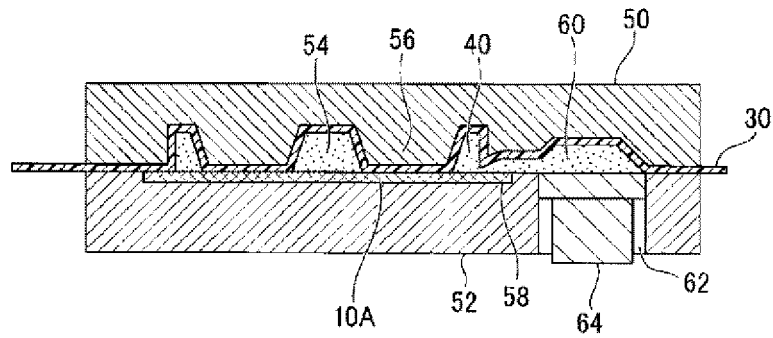
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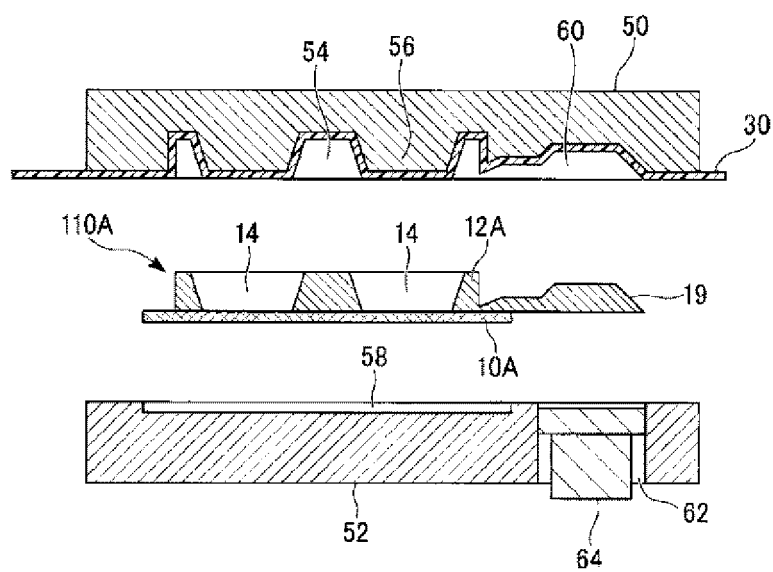
[図7]



[図8]

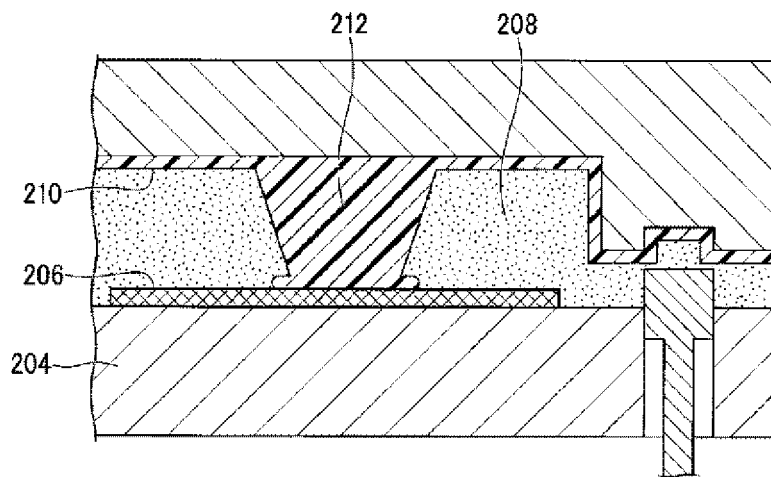


[図9]



A cross-sectional view of a semiconductor device. A substrate 204 is shown at the bottom, with a thin layer 206 on its top surface. A patterned layer 200 is formed on the top surface 202 of the substrate. A cross-hatched region 208 is located at the edge of the substrate 204.

[図13]



[図14]

